



SK10N65E-TF

650V N-Channel MOSFET

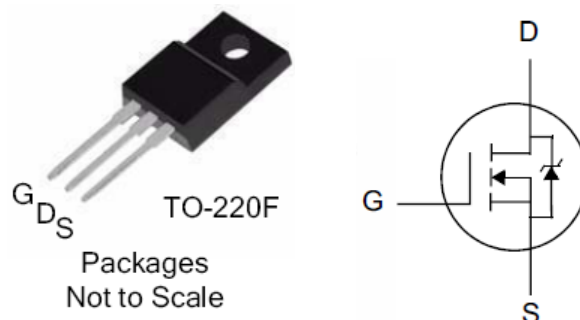
General Features

- Proprietary New Planar Technology
- $R_{DS(ON),typ.}=0.85\ \Omega @ V_{GS}=10V$
- Low Gate Charge Minimize Switching Loss
- Fast Recovery Body Diode

Applications

- Adaptor
- TV Main Power
- SMPS Power Supply
- LCD Panel Power

BV_{DSS}	$R_{DS(ON),typ.}$	I_D
650V	$0.85\ \Omega$	9A



Absolute Maximum Ratings

$T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	SK10N65E-TF	Unit
V_{DSS}	Drain-to-Source Voltage ^[1]	650	V
V_{GSS}	Gate-to-Source Voltage	± 30	
I_D	Continuous Drain Current	9	A
$I_D @ T_C=100^\circ\text{C}$	Continuous Drain Current @ $T_C=100^\circ\text{C}$	Figure 3	
I_{DM}	Pulsed Drain Current at $V_{GS}=10V$ ^[2]	Figure 6	
E_{AS}	Single Pulse Avalanche Energy	450	mJ
dv/dt	Peak Diode Recovery dv/dt ^[3]	5.0	V/ns
P_D	Power Dissipation	42	W
	Derating Factor above 25°C	0.33	W/ $^\circ\text{C}$
T_L T_{PAK}	Maximum Temperature for Soldering Leads at 0.063in (1.6mm) from Case for 10 seconds, Package Body for 10 seconds	300 260	$^\circ\text{C}$
$T_J \& T_{STG}$	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	SK10N65E-TF	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	2.97	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	100	



SK10N65E-TF

Electrical Characteristics

OFF Characteristics $T_J = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	650	--	--	V	$V_{GS}=0V, I_D=250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	--	--	1	μA	$V_{DS}=650V, V_{GS}=0V$
		--	--	100		$V_{DS}=520V, V_{GS}=0V, T_J=125^\circ\text{C}$
I_{GSS}	Gate-to-Source Leakage Current	--	--	+100	nA	$V_{GS}=+30V, V_{DS}=0V$
		--	--	-100		$V_{GS}=-30V, V_{DS}=0V$

ON Characteristics

$T_J = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance ^[4]	--	0.85	1.3	Ω	$V_{GS}=10V, I_D=4.5A$
$V_{GS(TH)}$	Gate Threshold Voltage	2.0	--	4.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
gfs	Forward Transconductance ^[4]	--	10	--	S	$V_{DS}=20V, I_D=9A$

Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{iss}	Input Capacitance	--	1600	--	pF	$V_{GS}=0V, V_{DS}=25V, f=1.0MHz$
C_{rss}	Reverse Transfer Capacitance	--	14	--		
C_{oss}	Output Capacitance	--	120	--		
Q_g	Total Gate Charge	--	30	--	nC	$V_{DD}=325V, I_D=9A, V_{GS}=0 \text{ to } 10V$
Q_{gs}	Gate-to-Source Charge	--	8.0	--		
Q_{gd}	Gate-to-Drain (Miller) Charge	--	10	--		

Resistive Switching Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	12	--	nS	$V_{DD}=325V, I_D=9A, V_{GS}=10V, R_G=4.7\Omega$
t_{rise}	Rise Time	--	15	--		
$t_{d(OFF)}$	Turn-Off Delay Time	--	40	--		
t_{fall}	Fall Time	--	17	--		



SK10N65E-TF

Source-Drain Body Diode Characteristics

$T_J=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Unit	Test Conditions
I_{SD}	Continuous Source Current ^[4]	--	--	9	A	Integral PN-diode in MOSFET
I_{SM}	Pulsed Source Current ^[4]	--	--	36		
V_{SD}	Diode Forward Voltage	--	--	1.5	V	$I_S=9\text{A}$, $V_{GS}=0\text{V}$
t_{rr}	Reverse recovery time	--	460	--	ns	$V_{GS}=0\text{V}$, $I_F=9\text{A}$, $di_F/dt=100\text{A}/\mu\text{s}$
Q_{rr}	Reverse recovery charge	--	1.5	--	μC	

Note:

[1] $T_J=+25^{\circ}\text{C}$ to $+150^{\circ}\text{C}$

[2] Repetitive rating; pulse width limited by maximum junction temperature.

[3] $I_{SD}=20\text{A}$ $di/dt < 100\text{A}/\mu\text{s}$, $V_{DD} < BV_{DSS}$, $T_J=+150^{\circ}\text{C}$.

[4] Pulse width $\leq 380\mu\text{s}$; duty cycles $\leq 2\%$.



Typical Characteristics

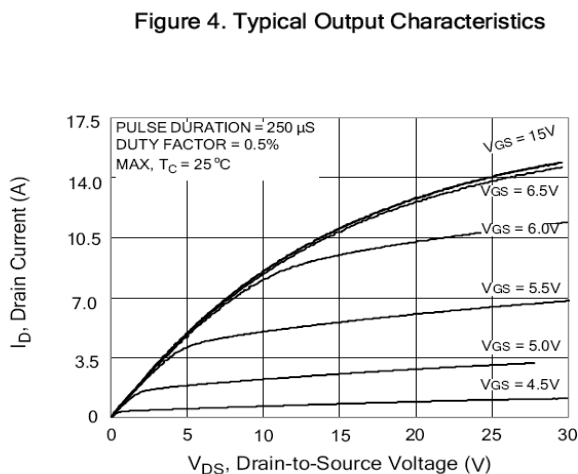
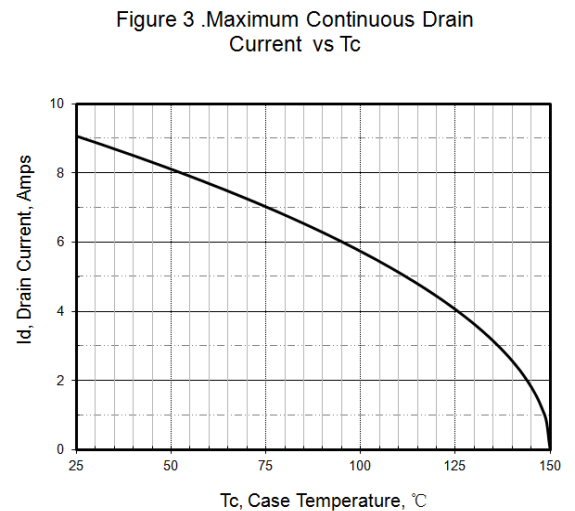
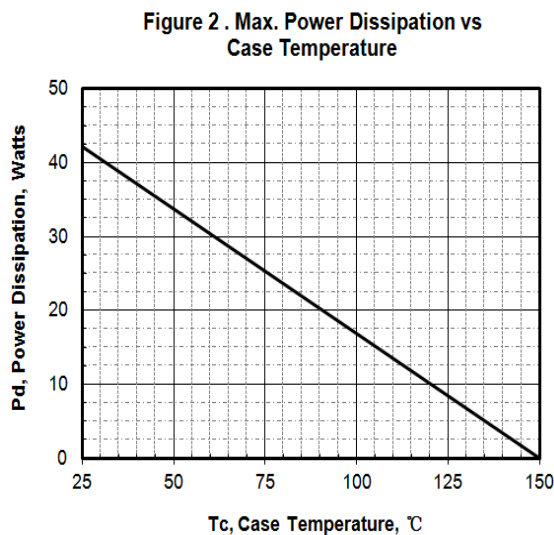
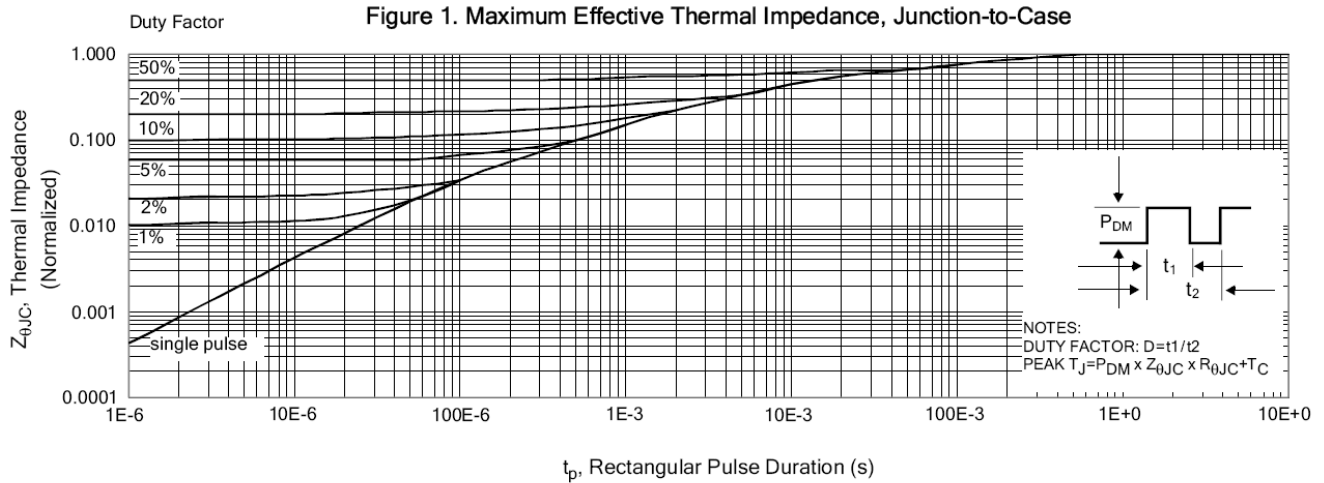
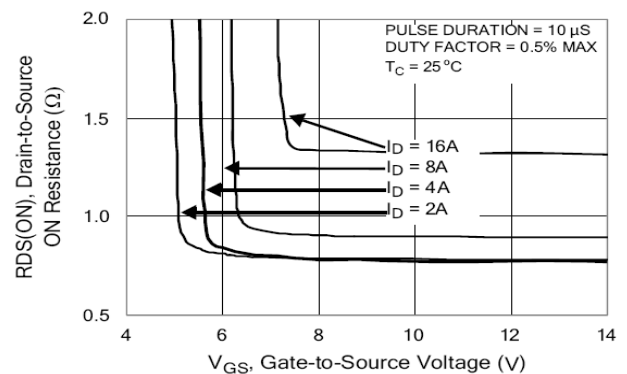
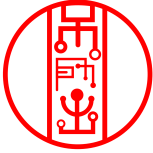


Figure 5. Typical Drain-to-Source ON Resistance vs Gate Voltage and Drain Current





SK10N65E-TF

Typical Characteristics(Cont.)

Figure 6. Peak Current Capability

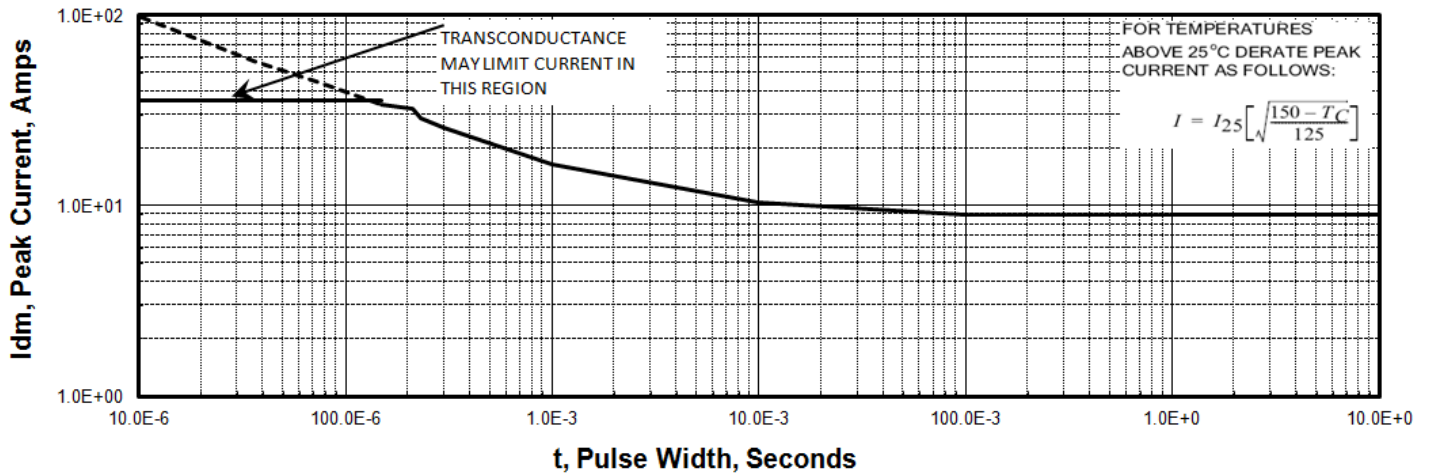


Figure 7. Typical Transfer Characteristics

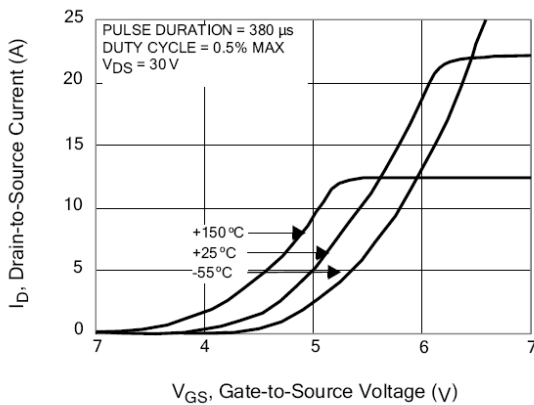


Figure 8. Unclamped Inductive Switching Capability

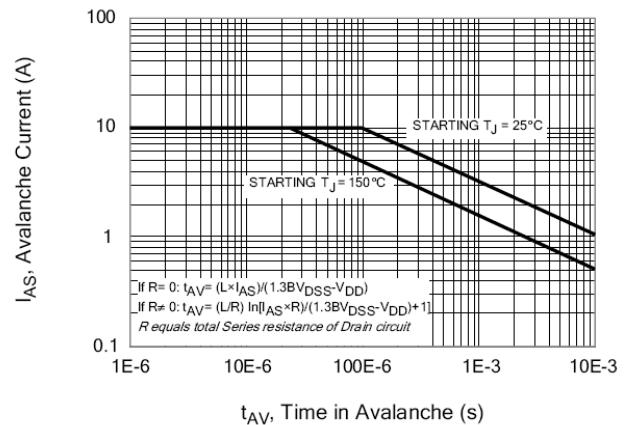


Figure 9. Typical Drain-to-Source ON Resistance vs Drain Current

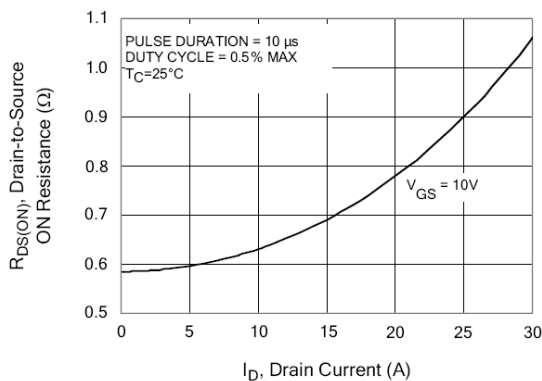
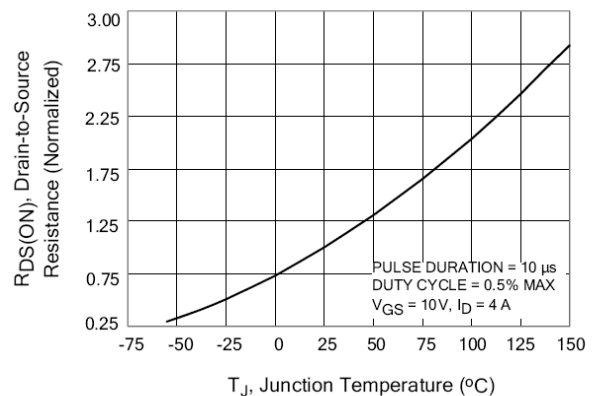


Figure 10. Typical Drain-to-Source ON Resistance vs Junction Temperature







Test Circuits and Waveforms

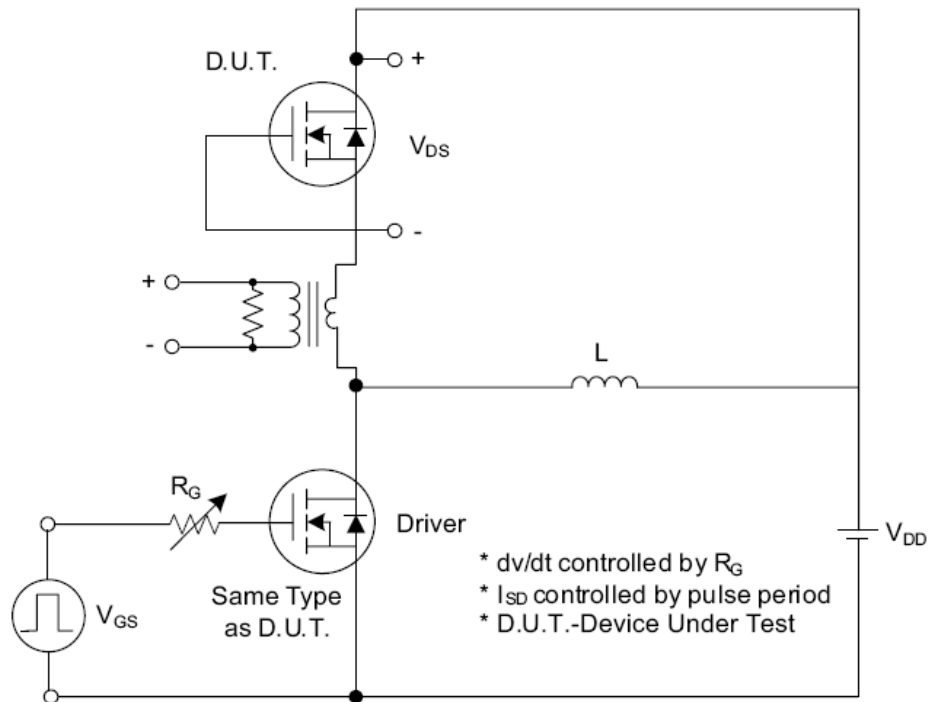


Fig. 1.1 Peak Diode Recovery dv/dt Test Circuit

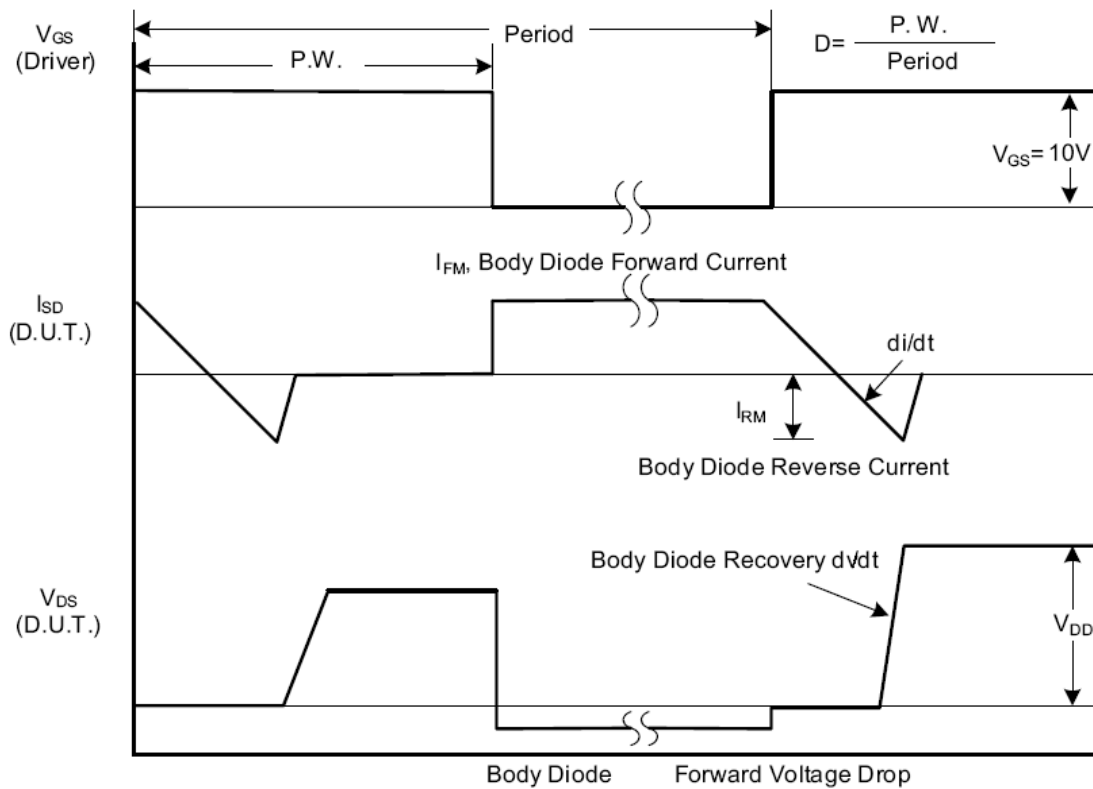


Fig. 1.2 Peak Diode Recovery dv/dt Waveforms



SK10N65E-TF

Test Circuits and Waveforms (Cont.)

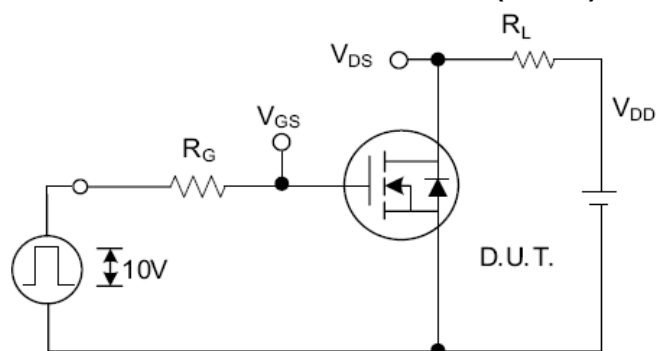


Fig. 2.1 Switching Test Circuit

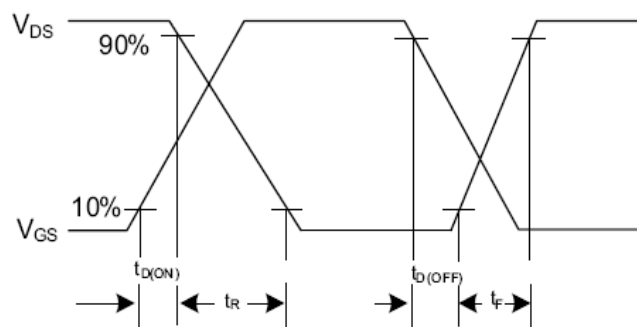


Fig. 2.2 Switching Waveforms

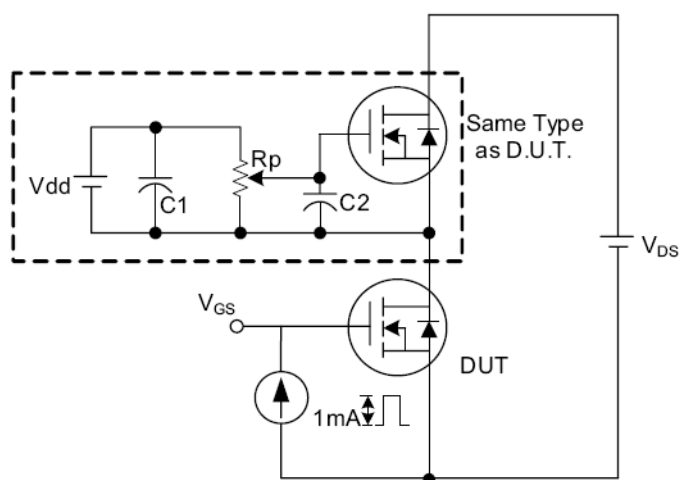


Fig. 3.1 Gate Charge Test Circuit

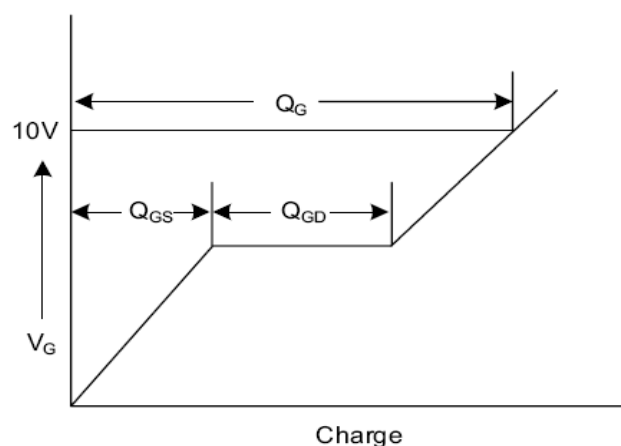


Fig. 3.2 Gate Charge Waveform

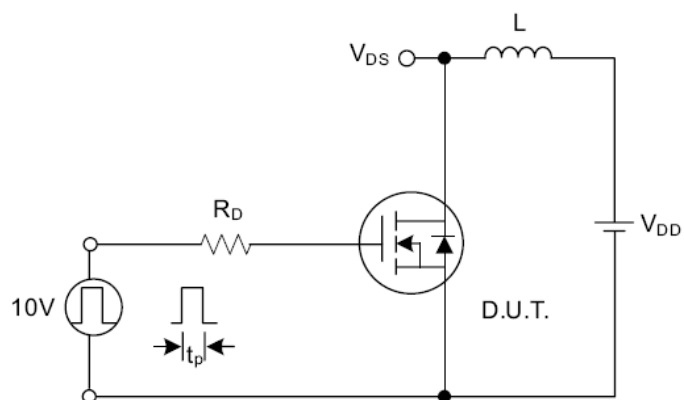


Fig. 4.1 Unclamped Inductive Switching Test Circuit

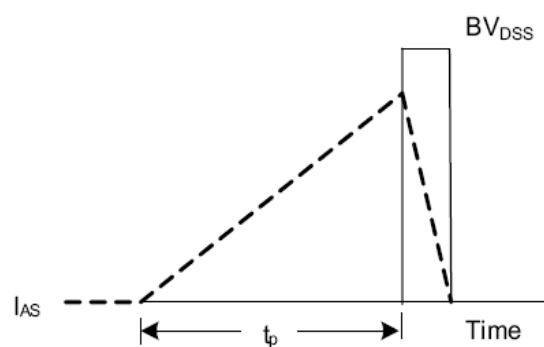
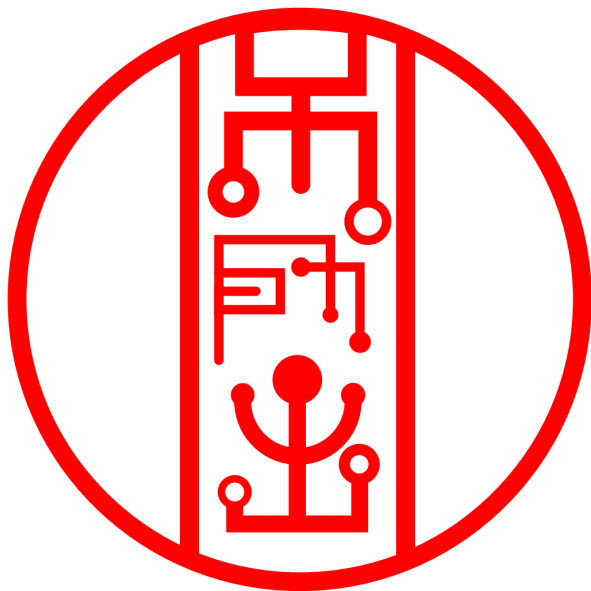


Fig. 4.2 Unclamped Inductive Switching Waveforms

PACKAGE OUTLINE

TO-220F



	Unit (mm)	
	MIN	MAX
A	9.70	10.30
B	15.50	16.10
B1	8.99	9.39
C	4.40	4.80
C1	2.15	2.55
D	2.50	2.90
E	0.70	0.90
F	0.40	0.60
G	1.12	1.42
H	3.40	3.80
L	12.6	13.6
N	2.34	2.74
Q	3.15	3.55
Φ P	3.00	3.30